

## Innovating Energy Technology

http://www.fujielectric.com/products/semiconductor/ Discrete IGBT

## Discrete IGBT (High-Speed W series) 650V / 30A

### Features

Low power loss Low switching surge and noise High reliability, high ruggedness (RBSOA, SCSOA etc.)

#### Applications

Uninterruptible power supply PV Power conditioner Inverter welding machine

#### Maximum Ratings and Characteristics

• Absolute Maximum Ratings (at T<sub>vi</sub> = 25 °C unless otherwise specified)

Parameter	Symbol	Value	Unit	Remarks
Collector-Emitter Voltage	VCES	650	V	
Gate-Emitter Voltage	V <sub>GES</sub>	± 20	V	
Transient Gate-Emitter Voltage		± 30		<i>t</i> ₀ < 1 µs
DC Collector Current	Ic@25	46	Α	<i>T</i> <sub>c</sub> =25°C
	I <sub>C@100</sub>	30	Α	<i>T</i> <sub>c</sub> =100°C
Pulsed Collector Current	I <sub>CP</sub>	120	Α	Note *1
Turn-Off Safe Operating Area	-	120	Α	V <sub>CE</sub> ≤ 650 V
				<i>T</i> <sub>vj</sub> ≤ 175°C
Max. Power Dissipation	Ptot	180	W	$T_c = 25^{\circ}C$
<b>Operating Junction Temperature</b>	Tvj	-40 ~ +175	°C	
Storage Temperature	T <sub>stg</sub>	-55 ~ +175	°C	



#### Equivalent circuit



(Out view: see to 5 page)

Note \*1 : Pulse width limited by  $T_{vjmax}$ .

#### • Electrical characteristics (at Tvj = 25 °C unless otherwise specified)

Parameter	Symbol	Conditions		min.	typ.	max.	Unit
Zero Gate Voltage Collector Current	ICES	V <sub>CE</sub> = 650 V, V <sub>GE</sub> = 0 V	$T_{vj} = 25^{\circ}C$	-	-	250	μA
•			<i>T</i> <sub>vj</sub> = 175°C	-	-	2	mA
Gate-Emitter Leakage Current	IGES	$V_{\rm CE} = 0 \text{ V}, V_{\rm GE} = \pm 20 \text{ V}$		-	-	200	nA
Gate-Emitter Threshold Voltage	V <sub>GE (th)</sub>	V <sub>CE</sub> = 20 V, <i>I</i> <sub>C</sub> = 30 mA		3.0	4.0	5.0	V
			<i>T</i> <sub>vj</sub> = 25°C	1.40	1.80	2.20	
Collector-Emitter Saturation Voltage	V <sub>CE (sat)</sub>	$V_{\text{GE}} = 15 \text{ V}, I_{\text{C}} = 30 \text{ A}$	<i>T</i> <sub>vj</sub> = 125°C	-	2.05	-	V
			<i>T</i> <sub>vj</sub> = 175°C	-	2.10	-	l
Input Capacitance	Cies	V <sub>CE</sub> = 25 V		1150	2300	3450	
Output Capacitance	Coes	$V_{GE} = 0 V$		33	66	99	pF
Reverse Transfer Capacitance	Cres	f = 1 MHz		25	50	75	
		V <sub>cc</sub> = 520 V					
Gate Charge	Q <sub>G</sub>	/c = 30 A		64	128	192	nC
	~	$V_{GE} = 15 \text{ V}$					
Turn-On Delay Time	t <sub>d(on)</sub>	$\frac{T_{\rm v_{\rm I}} = 25^{\circ} \rm C, \ V_{\rm cc} = 400 \ V}{I_{\rm c} = 15 \ \rm A, \ V_{\rm GE} = 15 \ \rm V}$		9	18	27	ns
Rise Time	tr			5.5	11	16.5	
Turn-Off Delay Time	t <sub>d(off)</sub>			74	148	222	
Fall Time	tı		$-R_{\rm G} = 10 \Omega$		11	16.5	
Turn-On Energy	Eon	Energy loss include "tail" and FWD reverse recovery.		0.06	0.12	0.18	
Turn-Off Energy	Eoff			0.07	0.15	0.23	mJ
Turn-On Delay Time	t <sub>d(on)</sub>	$T_{vj} = 150^{\circ}C, V_{cc} = 400 V$ $I_c = 15 A, V_{GE} = 15 V$ $R_G = 10 \Omega$ Energy loss include "tail" and FWD reverse recovery.		9	18	27	
Rise Time	tr			6	12	18	
Turn-Off Delay Time	t <sub>d(off)</sub>			89	178	267	ns
Fall Time	tr			8	16	24	
Turn-On Energy	Eon			0.10	0.21	0.32	mJ
Turn-Off Energy	Eoff			0.12	0.25	0.38	

#### • Thermal resistance characteristics

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Thermal Resistance, Junction-Ambient	Rth(j-a)	-	-	-	50	°C/W
Thermal Resistance, Junction to Case	Rth(j-c)	-	-	-	0.831	0/10

## Characteristics (Representative)



Figure 3. Typical output characteristics  $T_{yi}$ = 25°C



Figure 5. Typical transfer characteristics  $V_{CE}$  = 10 V









Figure 6. Gate threshold voltage  $I_{\rm C}$  = 30 mA,  $V_{\rm CE}$  = 20 V





Figure 9. Typical switching times vs.  $I_{c}$  $V_{cc}$  = 400 V,  $V_{GE}$  = 15 V,  $R_{G}$  = 10  $\Omega$ ,  $T_{vj}$  = 150°C



Figure 11. Typical switching losses vs.  $I_{c}$  $V_{cc}$  = 400 V,  $V_{GE}$  = 15 V,  $R_{G}$  = 10  $\Omega$ ,  $T_{vi}$  = 150°C





Figure 10. Typical switching times vs.  $R_{\rm G}$ 



Figure 12. Typical switching losses vs.  $R_{G}$  $V_{CC}$  = 400 V,  $V_{GE}$  = 15 V,  $I_{C}$  = 15 A,  $T_{vj}$  = 150°C



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### Figure 13. Reverse biased safe operating area

 $V_{\rm GE} = 15 \text{ V} / 0 \text{ V}, R_{\rm G} = 10 \Omega, T_{\rm vj} \le 175^{\circ} \text{C}$ 





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### Outline Drawings, mm



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